FORM PTO-1083				Ca., Do	ocket	No	PD-8	811
In re application Serial To.	Michio Asahina 07/780,455		•	Date:_	March	31, 19	93	
Filed: 1393	October 22, 1991		93 322	-3 ()	.1 :::06	ο .		
For:	SEMICONDUCTOR DEVI	ICE				o t	ŀ	
COMMISSIONER OF PATENTS Washington, D.C. 20231	S AND TRADEMARKS		15	Ju _r II	į į.		APR	ti B
Sir:						(_;		
Transmitted herewith is	s an amendment/reapo	onge in the	above-	identif	led a	nnlicat	ion	
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Respectfully submitted,

M. Finkelstein, 21,082

SPENSLEY HORN JUBAS & LUBITZ ATTORNEYS AT LAW 1880 CENTURY PARK EAST, FIFTH FLOOR LOS ANGELES, CALIFORNIA 90067 (310) 553-5050

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PATENT SAL PD-8811FWC

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

MICHIO ASAHINA

Serial No.: 07/780,455

Filing Date: October 22, 1991

For: SEMICONDUCTOR DEVICE

ART GROUP UNIT: 25

2508

APR 0 8 1993

EXAMINER:

S. Loke

AMENDMENT UNDER 37 C.F.R. § 1.116

Honorable Commissioner of Patents & Trademarks Washington, D.C. 20231

Dear Sir:

In response to the Examiner's Action dated January 4, 1993, kindly amend the above-identified application as follows:

IN THE CLAIMS:

Kindly cancel claim 26 and amend claim 25 as follows:

28. (AMENDED) A method of fabricating a semiconductor

device, comprising the steps of:

providing a substrate having a doped semiconductor region, the metal and a gate wiring, forming a lower conductor structure, and forming an insulating layer overlying said lower structure, and having at plating layer least one through opening extending to said lower conductor structure; and

forming an upper conductor structure on the insulating layer and causing the upper conductor structure to be connected to the lower conductor structure via the through opening;

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